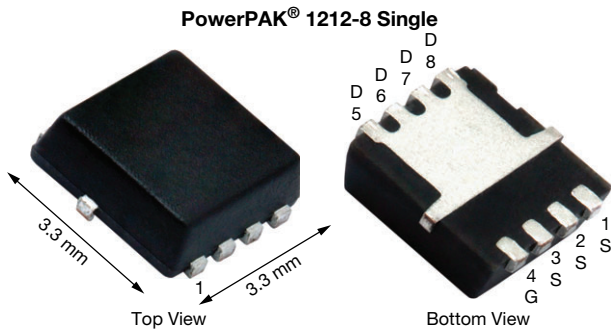


## N-Channel 20 V (D-S) MOSFET



### FEATURES

- TrenchFET® Gen IV power MOSFET
- Less than 1.1 mΩ in a package footprint of 10.89 mm<sup>2</sup>
- 2.5 V rated R<sub>DS(on)</sub>
- Optimized Q<sub>g</sub>, Q<sub>gd</sub>, and Q<sub>gd</sub>/Q<sub>gs</sub> ratio reduce switching related power loss
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

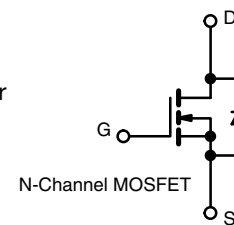


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	20
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V	0.00110
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 4.5 V	0.00145
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 2.5 V	0.00420
Q <sub>g</sub> typ. (nC)	18.2
I <sub>D</sub> (A)	162 <sup>a</sup>
Configuration	Single

### APPLICATIONS

- Synchronous rectification
- Synchronous buck converter
- Battery management
- Load switching



ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSA40DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V <sub>DS</sub>	20	V	
Gate-source voltage	V <sub>GS</sub>	+12 / -8	V	
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	162	A	
	T <sub>C</sub> = 70 °C	129		
	T <sub>A</sub> = 25 °C	43.7 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	35 <sup>b, c</sup>		
Pulsed drain current (t = 100 μs)	I <sub>DM</sub>	150	A	
Continuous source-drain diode current	T <sub>C</sub> = 25 °C	47	A	
	T <sub>A</sub> = 25 °C	3.3 <sup>b, c</sup>		
Single pulse avalanche current	L = 0.1 mH	20	A	
Single pulse avalanche energy	E <sub>AS</sub>	20	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	52	W	
	T <sub>C</sub> = 70 °C	33		
	T <sub>A</sub> = 25 °C	3.7 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	2.4 <sup>b, c</sup>		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) <sup>c</sup>		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	R <sub>thJA</sub>	24	33	°C/W
Maximum junction-to-case (drain)	R <sub>thJF</sub>	1.9	2.4	

### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 81 °C/W
- T<sub>C</sub> = 25 °C



<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10\text{ mA}$	-	18	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	-3.6	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6	-	1.5	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = +12 / -8\text{ V}$	-	-	100	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$	-	-	15	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	40	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	0.00092	0.00110	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	0.00120	0.00145	
		$V_{GS} = 2.5\text{ V}, I_D = 10\text{ A}$	-	0.00320	0.00420	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$	-	60	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{ISS}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	3415	-	$\mu\text{F}$
Output capacitance	$C_{OSS}$		-	1290	-	
Reverse transfer capacitance	$C_{RSS}$		-	72	-	
Total gate charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	35.2	53	nC
		$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	18.2	27.5	
Gate-source charge	$Q_{gs}$		-	7.3	-	
Gate-drain charge	$Q_{gd}$		-	3.6	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.4	0.85	1.4	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1\text{ }\Omega, I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	20	40	ns
Rise time	$t_r$		-	13	26	
Turn-off delay time	$t_{d(off)}$		-	40	80	
Fall time	$t_f$		-	10	20	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1\text{ }\Omega, I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$	-	12	24	
Rise time	$t_r$		-	5	10	
Turn-off delay time	$t_{d(off)}$		-	34	68	
Fall time	$t_f$		-	6	10	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	47	A
Pulse diode forward current	$I_{SM}$		-	-	150	
Body diode voltage	$V_{SD}$	$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$	-	0.73	1.1	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	-	32	64	ns
Body diode reverse recovery charge	$Q_{rr}$		-	21	42	nC
Reverse recovery fall time	$t_a$		-	16	-	ns
Reverse recovery rise time	$t_b$		-	16	-	

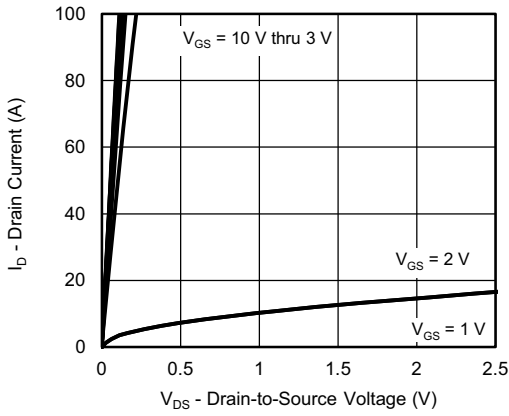
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing

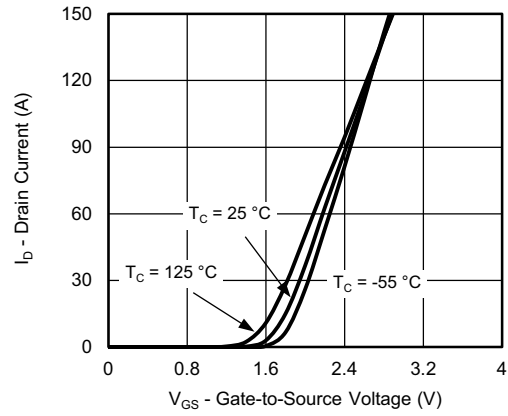
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



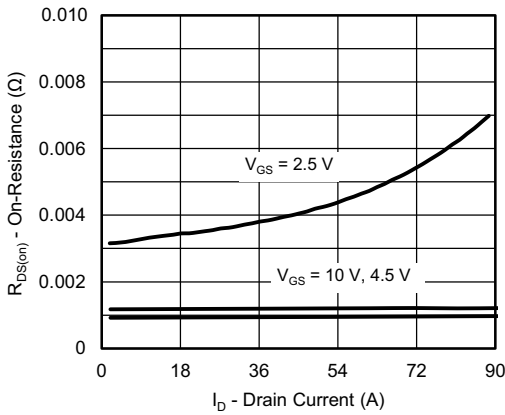
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



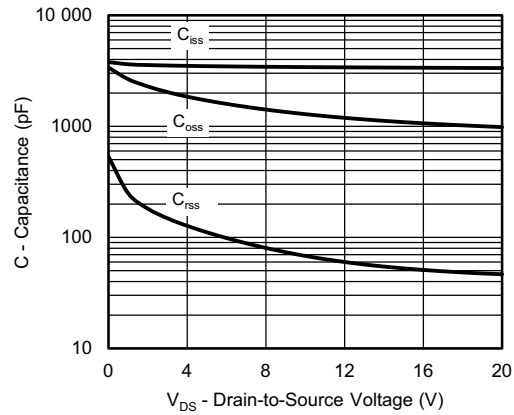
Output Characteristics



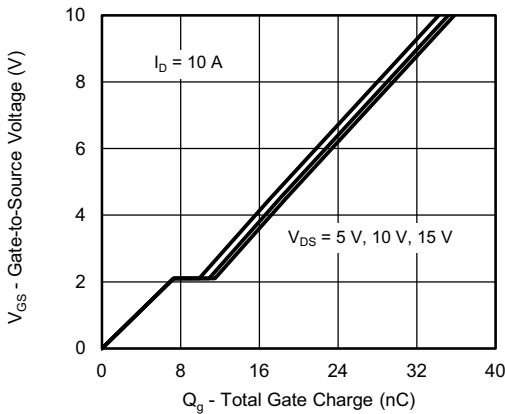
Transfer Characteristics



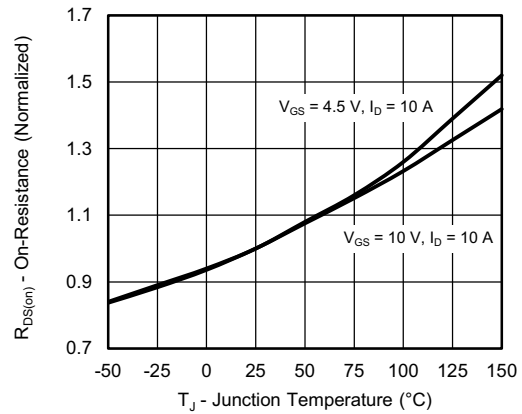
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



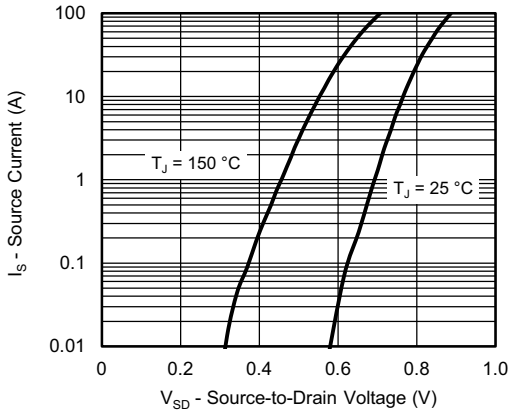
Gate Charge



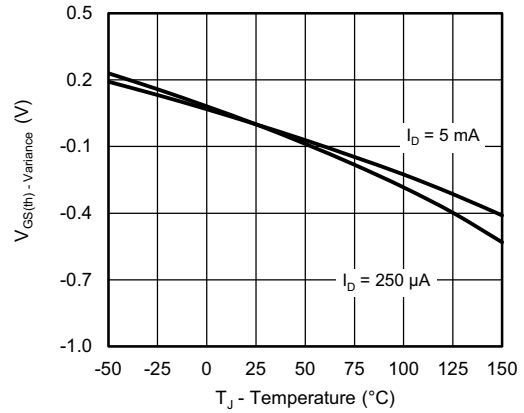
On-Resistance vs. Junction Temperature



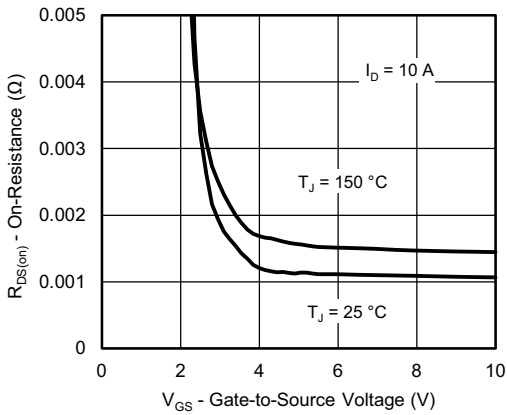
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



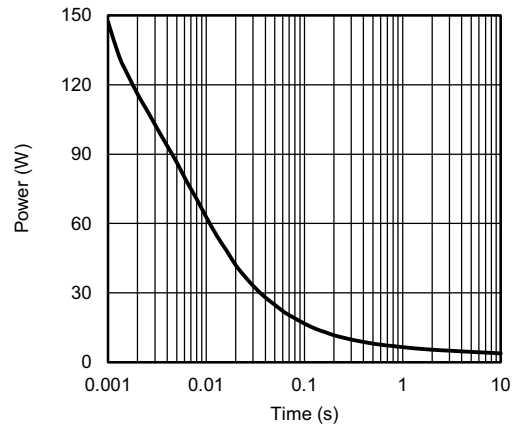
**Source-Drain Diode Forward Voltage**



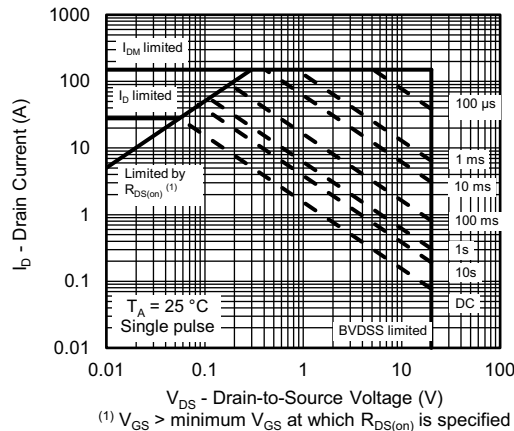
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



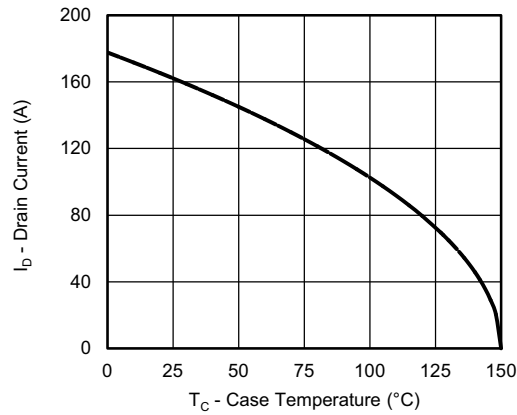
**Single Pulse Power, Junction-to-Ambient**



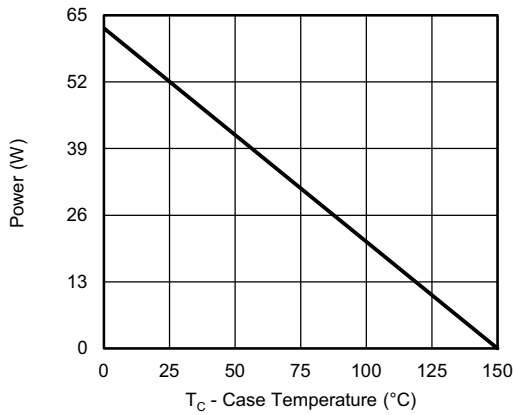
**Safe Operating Area, Junction-to-Ambient**



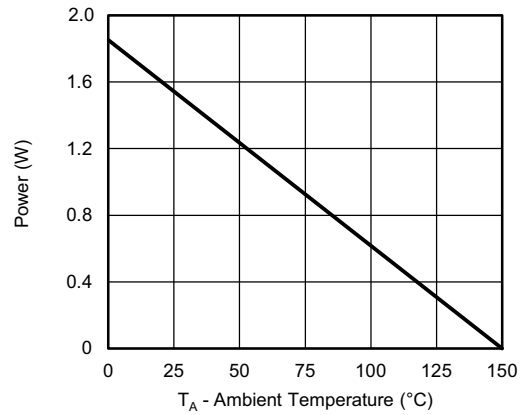
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



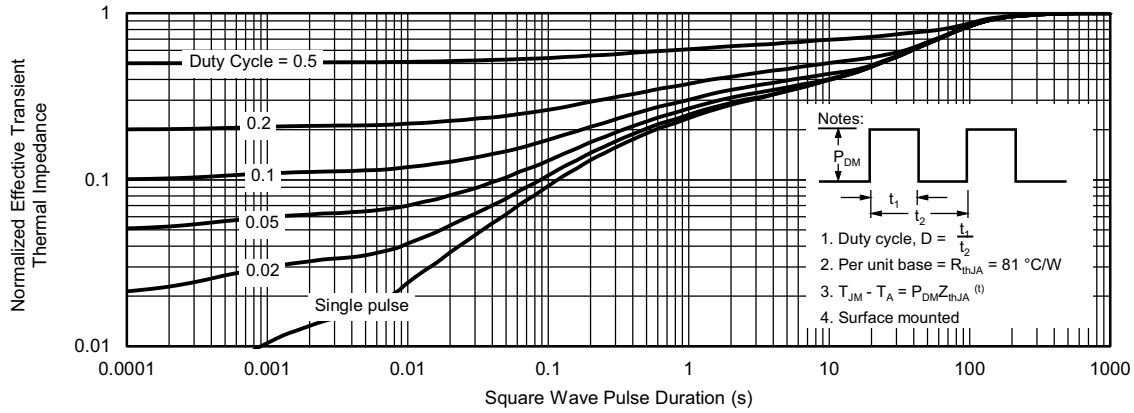
**Power, Junction-to-Ambient**

**Note**

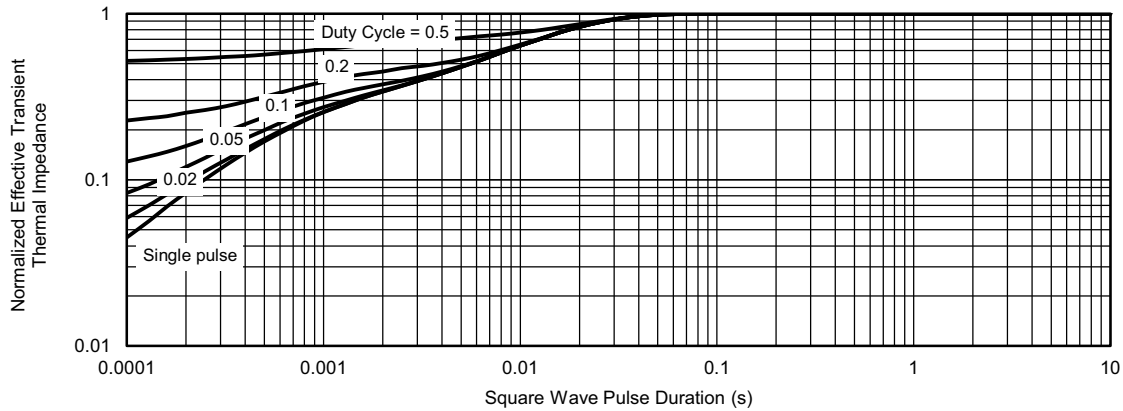
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK® 1212-8, (Single / Dual)



- Notes**
- 1. Inch will govern
  - [2] Dimensions exclusive of mold gate burrs
  - 3. Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1	0.00	-	0.05	0.000	-	0.002
b	0.23	0.30	0.41	0.009	0.012	0.016
c	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D3	0.48	-	0.89	0.019	-	0.035
D4	0.47 typ.			0.0185 typ		
D5	2.3 typ.			0.090 typ		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4	0.034 typ.			0.013 typ.		
e	0.65 BSC			0.026 BSC		
K	0.86 typ.			0.034 typ.		
K1	0.35	-	-	0.014	-	-
H	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: S16-2667-Rev. M, 09-Jan-17						
DWG: 5882						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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